APRII: THINGS TO DO AFTER LAYOUT

NYCU-EE IC LAB FALL 2024



Lecturer:

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Outline

- ✓ Power Verification
- ✓ Bonding Pads Insertion Flow
- ✓ Cell-Based Design Flow Review



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Power Component

✓ Dynamic Power

Switching Power

- $P = 0.5 * C_LV^2F*A,$
- C_L: output capacitance loading, V: voltage, F: frequency
- A: average switching activity from VCD or computed
- Charge and discharge the loading capacitive

✓ Internal Power (Short circuit power)

- Both NMOS and PMOS are turned on
- Calculated using *.lib file

✓ Static Power

✓ Leakage Power

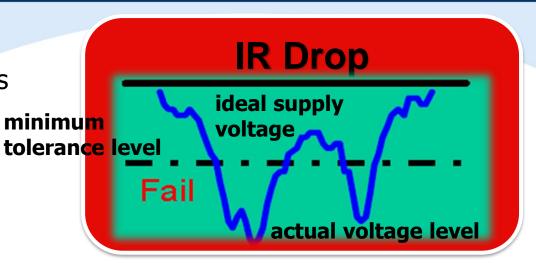
- Power consumed by device when no switching
- Calculated using *.lib file



Power Verification - Introduction

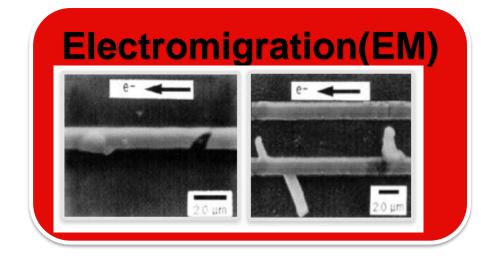
✓ IR Drop

Average or Instantaneous
 Power Issue



✓ Electromigration(EM)

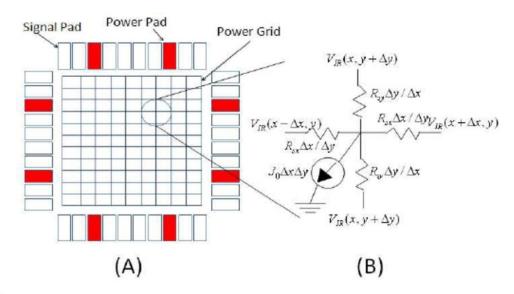
Long Term Power Density
 Problem



IR Drop (1/3)

✓ Power issue

- IR drop (IRD)
 - IR drop is the problem of voltage drop of the power and ground due to high current flowing through the power-ground resistive network
 - The drop in supply voltage over the length of the supply line



- (A) I/O Pad Location and Power Distribution
- (B) node model in the grid



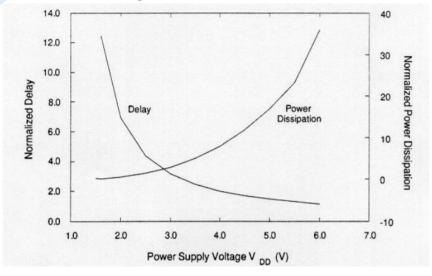
IR Drop (2/3)

✓ Power issue

IR drop (IRD)

 When there are excessive voltage drops in the power network or voltage rises in the ground network, the device will run at slower

speed



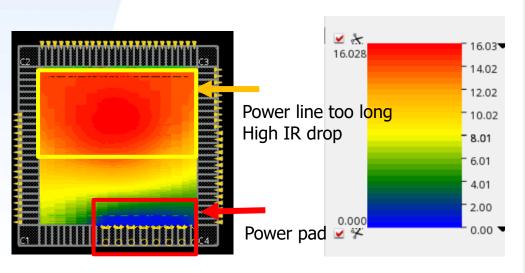
- As the process becoming more and more advanced, the IR drop turns to be an important issue.
- IR drop can cause the chip to fail due to
 - ◆ Performance (circuit running slower than specification)
 - Functionality problem (setup or hold violations)
 - ◆ Unreliable operation (less noise margin)

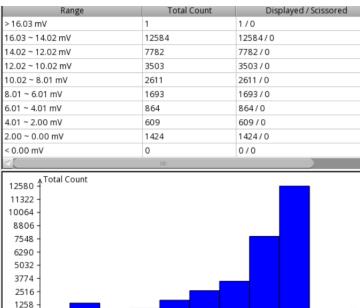


Power Verification - Introduction

✓ Power issue

- IR drop (IRD)
 - Prevention:
 - 1. Adding stripes to avoid IR drop on cell's power line
 - 2. Change the position of power pad to avoid long power line
 - 3. Use square-shaped Chip to avoid long power line
 - 4. Add decoupling cell





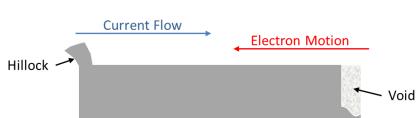


10.02 12.02 14.02 16.03 >16.03

Electro-Migration

✓ Electro-Migration (EM)

- EM is the unwanted transport of material due to movement of ions in a conductor, caused by a transfer of momentum from electrons to these ions.
- High-density current in a narrow metal wire may destroy the wire
- Performance Degradation
 - Increase/decrease in wire RC
- Can result in catastrophic failure
 - Open
 - Short
- EM analysis solution
 - Calculates the current on each wire and compares it to foundry EM rules.



Power Analysis - Method

✓ Vector: simulation waveform result for all gates

Vector-based

- Uses VCD (waveform file)
 - VCD is waveform file, like fsdb
- Requires:
 - Simulation is possible at the full-chip level
 - Simulation provides sufficient functional coverage of design
 - Vectors include those cause highest power consumption

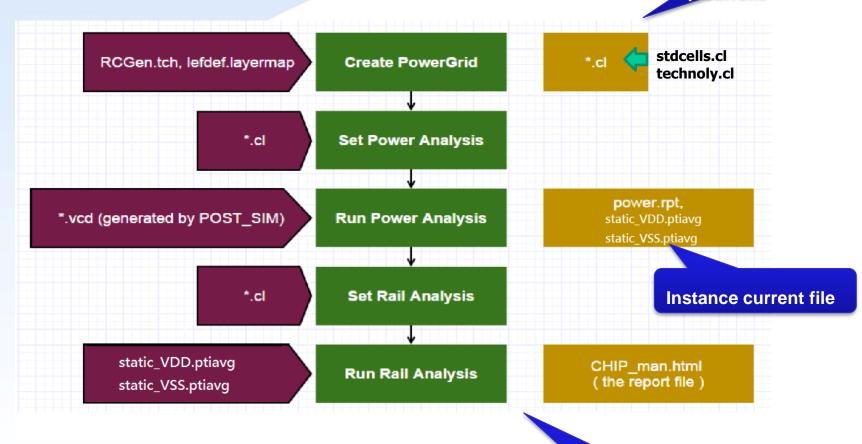
✓ Vector-independent

- Uses TWF (timing window file, generated by Static Timing Analysis)
 - Clock domain, skews, slack, arrival times of each pin.
- Requires:
 - A good estimation of input switching frequency



Power/Rail Analysis flow

PG library contains:
Tap location
Tap capacitance
Tap current



Power graph
- IR drop



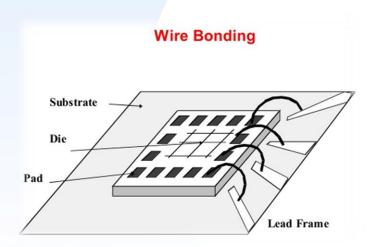
Outline

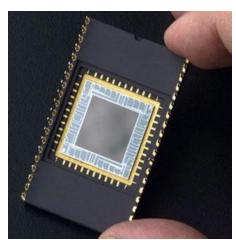
- ✓ Power Verification
- ✓ Bonding Pads Insertion Flow
- ✓ Cell-Based Design Flow Review

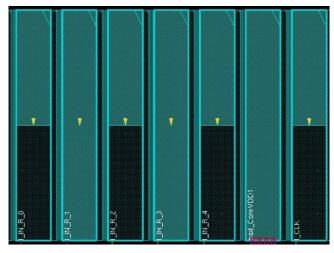


Bonding pads

- A bonding pad is used to connect the circuit on a die to a pin on a packaged chip
- Typically, the bonding pad is made from all the metal layers stacked on top of each other and connected through vias

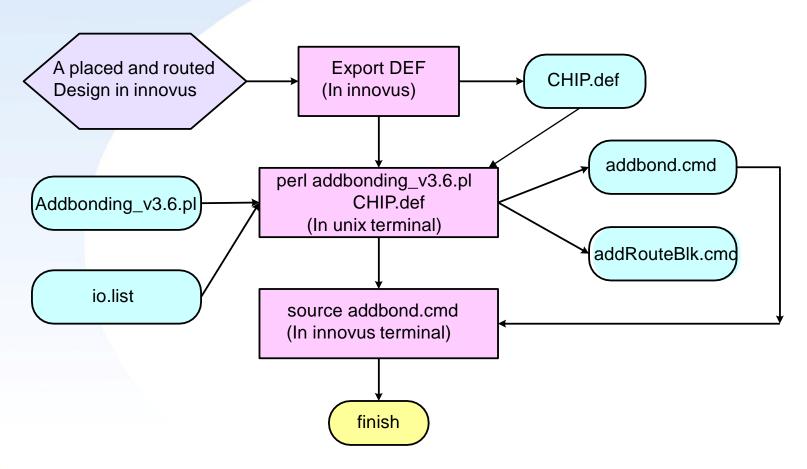






Bonding pads insertion flow

Flow & Script provided by manufacturer



Outline

- ✓ Power Verification
- ✓ Bonding Pads Insertion Flow
- ✓ Cell-Based Design Flow Review
 - LEF Files (.lef)
 - Library Files (.lib)

Data Preparation overview

✓ Library files

- Timing libraries (LIB)
 - fsa0m_a_generic_core_ff1p98vm4 0c.lib
 - fsa0m_a_generic_core_ss1p62v125c.lib
 - fsa0m_a_t33_generic_io_ff1p98vm 40c.lib
 - fsa0m_a_t33_generic_io_ss1p62v1 25c.lib
- Physical libraries (LEF)
 - fsa0m_a_generic_core.lef
 - fsa0m_a_t33_generic_io.lef
 - FSA0M_A_GENERIC_CORE_ANT_V 55.lef
 - FSA0M_A_T33_GENERIC_IO_ANT_ V55.lef
 - BONDPAD.lef
- RC extraction
 - u18_Faraday.CapTbl
 - icecaps.tch

- CeltIC libraries
 - u18_ss.cdb
 - u18 ff.cdb
- GDSII layout
 - umc18.gds
 - umc18io3v5v_6lm.gds

Timing constraint files

- Generate timing constraint files from Design Complier
 - dc_shell-t> write_sdc CHIP.sdc

Design netlist files

- Synthesized design netlist
 - designName_SYN.v
- Chip design netlist (combine designName_SYN.v & CHIP_SHELL.v)
 - CHIP SYN.v
- IO pad location file
 - CHIP.io



✓ What is lef?

- Library Exchange Format (LEF)
- LEF defines the elements of an IC process technology and associated library of cell models.
- LEF file can be divide into two part: technology and physical macros

Technology

 A technology LEF file contains all of the LEF technology information for a design, such as placement and routing design rules, and process information for layers.

✓ Physical Macros

✓ – Contains the macro and standard cell information for a design.

Technology LEF file

Process Technology

- Layers
 - Poly
 - Metal
 - Via
- Design rule
 - Net width
 - Net spacing
 - Area
- /*Parasitic
 - Resistance
 - Capacitance*/

✓ APR Technology

- Site
- Pitch
- Default direction
- Via rule

LAYER met1

TYPE
ROUTING;
WIDTH 0.240;
MAXWIDTH 9.0;
AREA 0.1764;
THICKNESS 0.528;

END met1

SPACING

SAMENET met1 met1 0.240; SAMENET met2 met2 0.280 STACK;

END SPACING

SITE umc6site

SYMMETRY
y; CLASS
CORE;
SIZE 0.660 BY 5.040;
END umc6site

[VERSION statement] [BUSBITCHARS statement] [DIVIDERCHAR statement] [UNITS statement] [MANUFACTURINGGRID statement] [USEMINSPACING statement] [CLEARANCEMEASURE statement:] [PROPERTYDEFINITIONS statement] [LAYER (Nonrouting) statement | LAYER (Routing) statement] ... [SPACING statement] [MAXVIASTACK statement] [VIA statement] ... [VIARULE statement] ... [VIARULE GENERATE statement] ... [NONDEFAULTRULE statement] ... [SITE statement] ... [BEGINEXT statement] ... [END LIBRARY]

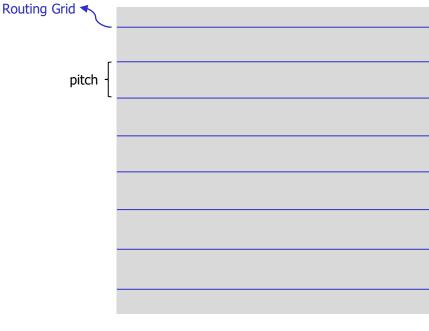


Pitch

✓ Pitch

- The distance between routing grids
- Reduce routing complexity
- Avoid DRC violation





Cell library LEF file

Define physical data for

- Standard cells
- I/O pads
- Memories
- Other hard macros

✓ Describe abstract shape

 A cell library LEF file can include any of the statements as shown in right hand side

```
MACRO
macroName [
CLASS
 { COVER [BUMP]
  RING
  BLOCK [BLACKBOX | SOFT]
  PAD [INPUT | OUTPUT | INOUT | POWER | SPACER | AREAIO]
  CORE [FEEDTHRU | TIEHIGH | TIELOW | SPACER | ANTENNACELL | WELLTAP]
  ENDCAP {PRE | POST | TOPLEFT | TOPRIGHT | BOTTOMLEFT | BOTTOMRIGHT}
[FOREIGN foreignCellName [pt [orient]];] ...
[ORIGIN pt;]
[EEQ macroName;]
[SIZE width BY height;]
[SYMMETRY {X | Y | R90} ...;]
[SITE siteName [sitePattern];] ...
[PIN statement] ...
[OBS statement] ...
[DENSITY statement] ...
[PROPERTY propName propVal;] ...
END macroName
```

✓ The units, operation conditions and template table are defined in the begin of LIB file

```
ibrary (NangateOpenCellLibrary)
   Documentation Attributes */
                                       : "Thu 10 Feb 2011, 18:11:58";
date
revision
                                       : "revision 1.0";
   General Attributes
technology
                                         (cmos);
delay model
                                       : table lookup;
in place swap mode
                                       : match footprint;
 library features
                                         (report delay calculation, report power calculation);
 /* Units Attributes *,
 time unit
                                         "lns"
leakage power unit
                                         "lnW"
voltage_unit
current_unit
                                                      lu table template (Timing 7 7)
pulling resistance unit
                                                             variable 1 : input net transition;
capacitive load unit
                                                             variable 2 : total output net capacitance;
 /* Operation Conditions
                                                             index 1 ("0.0010,0.0020,0.0030,0.0040,0.0050,0.0060,0.0070")
nom process
                                                             index 2 ("0.0010,0.0020,0.0030,0.0040,0.0050,0.0060,0.0070")
nom temperature
                                       : 125.00;
nom voltage
 voltage_map (VDD,0.95)
voltage map (VSS.0.00)
  efine(process corner, operating conditions, string)
operating conditions (slow) {
  process corner
                        "SlowSlow":
  process
                       : 1.00;
   voltage
   temperature
 default operating conditions : slow;
```

✓ LIB file contains

- Cell area
- Cell Leakage power
- Rise and fall capacitance of pins
- Timing information
- Internal power

```
(AND2 X1) {
drive strength
                          : 1.064000;
 og pin(VDD) (
         voltage name
         voltage name
     leakage power
                            15.154826;
 leakage power ()
                         : "!A1 & !A2";
 leakage power (
                         : "!A1 & A2";
 eakage power
                         : "A1 & !A2";
 eakage power
                         : "A1 & A2";
         direction
         related power pin
         related ground pin
         capacitance
                                   : 0.894757
         fall capacitance
                                   : 0.894757
         rise capacitance
```

✓ The timing information in LIB files

- Cell rise and cell fall
- Rise transition and fall transition

```
lu_table_template (Timing_7_7) {
    variable_1 : input_net_transition;
    variable_2 : total_output_net_capacitance;
    index_1 ("0.0010,0.0020,0.0030,0.0040,0.0050,0.0060,0.0070");
    index_2 ("0.0010,0.0020,0.0030,0.0040,0.0050,0.0060,0.0070");
```

```
index 1 ("0.00231025,0.0112628,0.0426883,0.102700,0.196195,0.327379,0.506
         "0.365616,1.893040,3.786090,7.572170,15.144300,30.288700,60<mark>.57740</mark>
        "0.0630239.0.0787480.0.0961212.0.129093.0.193632.0.321810.0
        "0.0674459,0.0831711,0.100537,0.133506,0.198055,0.326241,0
        "0.0840800,0.0996979,0.116960,0.149818,0.214346,0.342599,0.598289"
        "0.111098,0.127055,0.144257,0.176866,0.241183,0.369419,0.625170"
        "0.137221,0.154429,0.171997,0.204249,0.268543,0.396458,0.652147"
        "0.158896,0.178441,0.197069,0.229757,0.293570,0.421467,0.676922"
        "0.174683,0.196972,0.217621,0.251499,0.315047,0.442340,0.697757
         "0.00231025,0.0112628,0.0426883,0.102700,0.196195,0.327379,0.500000
         "0.365616,1.893040,3.786090,7.572170,15.144300,30.288700,60<mark>.577400"</mark>
          .0142179.0.0179662.0.0220337.0.0295478.0.0439247.0.0728803.0
        "0.0142202,0.0179650,0.0220353,0.0295435,0.0439265,0.0728882
        "0.0142401,0.0180012,0.0220653,0.0295620,0.0439313,0.0728830,0.133239
        "0.0152201,0.0186282,0.0225258,0.0298637,0.0441023,0.0729622<mark>,0.133254</mark>
        "0.0205299,0.0236322,0.0270182,0.0336077,0.0467309,0.0742211,0.133584
        "0.0268061,0.0300308,0.0332223,0.0393239,0.0516523,0.0780366,0.135619
        "0.0337402,0.0373263,0.0406222,0.0464392,0.0579323,0.0828138
```

What will happen if the value is out of range?

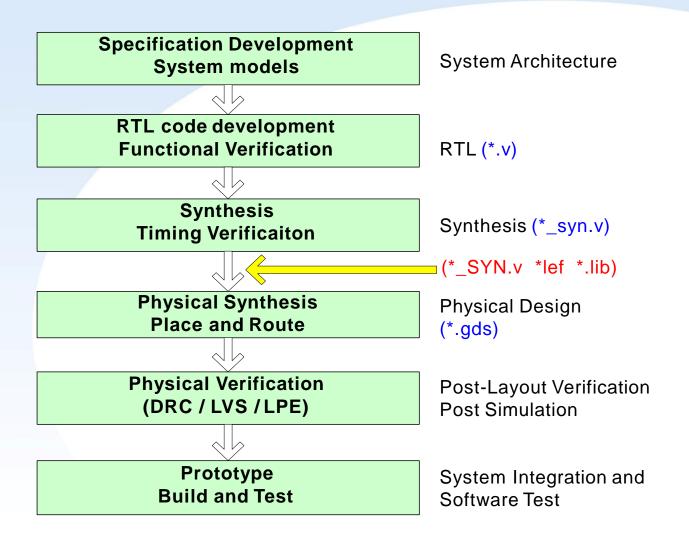
✓ The internal power information in LIB files

- Defined at each input pin
- Fall power and rise power

```
internal power ()
        related pin
        fall power(Power
                         ("0.00231025,0.0112628,0.0426883,0.102700,0.196195,0.327379,<mark>0.500000"</mark>
                 index 2 ("0.365616,3.767000,7.534000,15.068000,30.136000,60.272000,120.5
                 values ("4.457832,4.788072,5.028714,5.301675,5.524108,5.672181,5.743632
                          "4.446709,4.758343,4.987298,5.263321,5.489568,5.641210,5.704<mark>971</mark>
                          "4.371115,4.709637,4.935650,5.194484,5.422401,5.580039,5.645<mark>772"</mark>
                          "4.391769,4.694037,4.926985,5.181429,5.415031,5.571611,5.645<mark>876"</mark>
                         "4.493645,4.790255,5.021510,5.280662,5.522565,5.687319,5.762655"
                         "4.700944,4.900496,5.100309,5.353765,5.684057,5.917852,6.013548"
                          "5.077164,5.216876,5.371162,5.597479,5.913700,6.180814,6.371565
                         ("0.00231025,0.0112628,0.0426883,0.102700,0.196195,0.327379,<mark>0.50000</mark>0
                         ("0.365616,3.767000,7.534000,15.068000,30.136000,60.272000,120
                         ("3.050122.3.245451.3.348436.3.383495.3.410116.3.547264.3.476027
                          "3.013344,3.231263,3.325017,3.360157,3.483347,3.508233,3.573011"
                          "2.986118,3.189128,3.265965,3.330565,3.347222,3.486957,3.419<mark>327</mark>
                          "2.955822,3.140775,3.227351,3.277662,3.243906,3.384560,3.460445"
                         "3.009854,3.183423,3.252503,3.238903,3.235337,3.371907,3.452974"
                          "3.163226,3.359162,3.417024,3.391950,3.391603,3.383149,3.467371
                          "3.406716.3.630032.3.686185.3.676410.3.630300.3.667160.3.604<mark>747</mark>
```



Cell-based Design Flow





Physical Verification

✓ Physical verification

- Verify DRC and LVS with Calibre
- Fix errors with Virtuoso manually
- Provide GDS2 file to foundry(UMC \ TSMC) for manufacturing

Appendix: Bonding pads insertion steps

- ✓ During the APR flow, save → DEF→CHIP.def
- Execute "perl addbonding_v3.6.pl CHIP.def"
- ✓ Back to the Innovus, check the io.list
- ✓ When the APR flow finished, execute "source bondPads.cmd"
- ✓ There will be some cells on the IO PAD